# NATERIALY PLISSN 0209-0058 ELECTRONIC MATERIALS



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INSTYTUT TECHNOLOGII MATERIAŁÓW ELEKTRONICZNYCH INSTITUTE OF ELECTRONIC MATERIALS TECHNOLOGY

http://rcin.org.pl



Institute of Electronic Materials Technology

# Laboratory of Epitaxy

WE OFFER:

# Silicon epitaxial wafers with parameters:

2 - 10 μm ± 4% / 0.005 – 5 Ωcm ± 10% 10 - 50 μm ± 5% / 5 – 100 Ωcm ± 15% 50 - 100 μm ± 8% / 100 – 300 Ωcm ± 20%

and also:

Measurements of the resistivity profile (carrier concentration) using the spreading resistance method in a point contact on a bevelled sample.

Measurements of the properties of defect centres in semiconductor materials, using the DLTS, HRPITS and EPR methods.

# MATERIAŁY ELEKTRONICZNE ELECTRONIC MATERIALS

## QUARTERLY

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### WARSAW ITME 2017

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## MATERIAŁY ELEKTRONICZNE ELECTRONIC MATERIALS

## **CONTENTS 4** Effect of Ti and Zr additions on wettability and work of adhesion in Ag/C system

Wettability in the silver/carbon system was examined by the sessile drop method under vacuum at the temperature of 1243 K. Vitreous carbon, diamond and graphite were used as solid substrates. After wettability tests, the solidified Ag/C and Ag-X/C (X - 1 wt.% Ti or Zr) couples were subjected to structural characterization by SEM and EDX analysis. Liquid pure silver does not wet these substrates and shows week adhesion, regardless of the type of the carbon material used. The introduction of 1 wt.% carbide forming additions Ti or Zr into silver changes dramatically the interaction in the Ag/C system leading to the formation of continuous reaction product layers (TiC<sub>x</sub> and ZrC<sub>x</sub>, respectively) at the drop/substrate interface. These interfacial layers are responsible for good wetting and high work of adhesion between AgTi1 and AgZr1 alloys and all types of carbon materials examined in this study.



#### 12 The use of thermal mapping in evaluation of mechani cally induced electrical degradation of graphene based transparent heaters

The purpose of this study is to investigate temperature distributions of graphene-based transparent heaters deposited on glass. Furthermore it analyses the influence of layer discontinuities such as scratches and cracks on the performance of Joule-heated samples. Graphene mechanical strength was examined by the nanoscratch method at incremental loads using a ball on a flat sample surface. In the case of the controlled load several scratches were produced on the graphene surface. Tribological tests were conducted at different constant loads. The paper presents scanning electron micrograph (SEM) observations of the modified graphene surface. Infrared imaging of Joule-heated samples indicates a significant uniformity deterioration of the thermal maps due to the current flow alteration in the presence of structural imperfections. The results obtained in the course of this study give new insight into the role of defects such as cracks or discontinuities in the overall performance of graphene transparent layers.

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## 18 Evaluation of hydrophobic properties of organic layers modified with graphene flakes

The paper presents the results of our research on graphene composites with organic polymers in various media. The following composites have been tested: PVDF/DMF/GR, PVDF/NMP/GR, PVDF/acetone/toluene/GR and PMMA/GR. The main purpose of this study is to evaluate hydrophobic properties of the selected materials by the contact measurements angle using the static method. The highest obtained value of the contact angle approached 180° for a superhydrophobic composite PVDF/acetone/toluene/GR.

D. Wójcik-Grzybek, K.Frydman, N. Sobczak, R. Nowak, A. Piątkowska, K. Pietrzak

> A. Kozłowska, G. Gawlik, A. Piątkowska, A. Krajewska, W. Kaszub

B. Stańczyk, K. Góra, K. Jach, L. Dobrzański



Sample from dr Katarzyna Jach.

#### On the cover:

Ceramic foams made from silicon carbide and polyurethane matrix used to their production. Application: filters, catalyst carriers, ceramic-metal composites component





### EDITORIAL OFFICE ADDRESS

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The Institute of Electronic Materials Technology develops advanced innovative production technologies of materials characterized by a perfect crystallographic structure and excellent properties, as well as components based on these materials. The scope of R&D activities carried out covers the following areas: Materials for next-generation components: Materiais for electronics: graphene;
topological insulators;
materials for spintronics; • silicon monocrystals (standard Si wafers and Si wafers with special properties); porous silicon; self-organising materials; silicon foils; photonic crystals, including plasmonic materials · epitaxial layers on silicon; and metamaterials. · SiC wafers and SiC epitaxial layers; nanopowders and polymer-based powders, pastes and inks for printed electronics; Materials for energy generation, storage and transfer: photosensitive pastes; wide gap semiconductors, including silicon carbide for GaN HEMT transistors; piezoelectric crystals;ceramic-metal composites; semiconductor-doped glass optical fibres super-pure metals. semiconductor-doped glass optical i for photovoltaics;
eutectic materials for photovoltaics;
SiC wafers and SiC epitaxial layers;
glass-ceramic seals for fuel cells;
thermosolocitic materials; Components: ITME has elaborated a great number of innovative electronic components based on the manufactured thermoelectric materials; inert matrices for a safe storage of radioactive waste;
electrode materials for lithium ion batteries; materials, for instance: · ceramic-metal composites and FGMs. optical fibres (active and photonic), filters, diffractive lenses, two-dimensional photonic microstructures; passive elements on membranes (sensors); Materials for photonics: · filters, resonators, sensors and actuators based on materials for III-V based semiconductor lasers (obtained surface acoustic waves; using GaAsP, InGaP, AlGaAs, GaAs, GaSb and InP), · semiconductor devices (lasers, transistors, photodetectors, Schottky diodes);
solid state lasers and microlasers. wafers, epitaxial structures; GaN-based epitaxial structures; materials for solid state lasers, produced using strontium-calcium niobate; The manufacture of state of the art components is possible at ITME due to high-tech equipment infrared photodetectors and UV photodetectors; oxide crystals for lasers, passive Q modulators, scintillators, electro-optical and piezoelectric devices, substrates for superconducting HTSc layers; enabling: design and manufacture of masks; glass and ceramics with carefully designed spectral • deposition of dielectric thin films (Si0<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, AIN);

- characteristics, including transparent ceramics;
- diffractive optical elements and microlenses;
- nanostructured thin layers;
- luminescent nanopowders and nanocrystals;
- optical fibres and waveguides, including active and photonic fibres.
- multilayer metallization;
- use of lithography: contact printing using deep UV,
- use of https://www.endocryptic.com/ reactive ion etching and controlled sidewall etching.

#### Advanced methods of material properties investigation:

#### The characterization of materials is performed at ITME by the following methods:

- standard chemical analysis and spectral instrumental methods (flame atomie emission spectrometry, atomie absorption spectroscopy, ultraviolet to far-infrared spectroscopy);
- Mössbauer spectroscopy (conventional, conversion electron method, X radiation method and unique "rfMössbauer" method developed at ITME);
- X-ray powder diffraction using the Rietveld method, High Resolution X-ray diffraction, X-ray reflectometry and X-ray diffraction topography;
- scanning electron microscopy and a method based on synchrotron radiation;
- electron paramagnetic resonance;
- atomie force microscopy;
  standard thermal methods (high-temperature)
- microscopy, thermogravimetry, differentialthermal analysis, dilatometry, etc.) and X-ray methods; mechanical methods (testing resistance, friction,
- hardness, etc.);
- optical methods (microscopy, absorption, reflectometry).

Methods of electronic and photonic components investigation:

ITME tests optoelectronic, microelectronic and piezoelectric devices, using special techniques enabling the characterization of components, including:

- I-V and C-V measurements;
- deep level transient spectroscopy;
- impedance measurements and the measurements of scattering matrix elements up to the frequency of 20 Ghz;
- noise measurements;
- · analysis of operational parametres of lasers and photodetectors.